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Diodes Incorporated DMN2041UFDB-7

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Datasheet of DMN2041UFDB-7 - MOSFET 2N-CH 20V 4.7A 6UDFN

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DMN2041UFDB

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

Device	V _{(BR)DSS}	R _{DS(ON) max}	I _{D MAX} T _A = +25°C
N-Channel	20V	$40 \text{m}\Omega$ @ $V_{GS} = 4.5V$	4.7A
N-Chaine	20 V	$65m\Omega @ V_{GS} = 2.5V$	3.7A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Power Management Functions
- Portable Power Adaptors

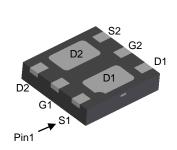
Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

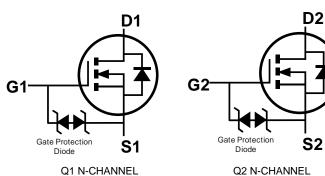
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)





U-DFN2020-6

Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2041UFDB -7	U-DFN2020-6	3,000/Tape & Reel
DMN2041UFDB -13	U-DFN2020-6	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

U-DFN2020-6



D7 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014) M = Month (ex: 9 = September)

Date Code Key

Year	201	4	2015		2016	20	17	2018		2019	2	2020
Code	В		С		D		Ξ	F		G		Н
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	20	V	
Gate-Source Voltage		V_{GSS}	±12	V	
Continuous Drain Current (Note EVV 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	4.7 3.8	А
Continuous Drain Current (Note 5) V _{GS} = 4.5V	t < 5s	$T_A = +25$ °C $T_A = +70$ °C	I _D	6.1 4.9	А
Maximum Continuous Body Diode Forward Curre	ent (Note 5)	Is	2	Α	
Pulsed Drain Current (10µs pulse, duty cycle = 1	%)	I _{DM}	20	Α	

Thermal Characteristics

Characteristic		Symbol	Value	Units	
Total Power Dissipation (Note 5)	Steady State	D-	1.4	W	
Total Power Dissipation (Note 5)	t < 5s	P _D	2.2		
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	ם	92		
Thermal Resistance, Junction to Ambient (Note 5)	t < 5s	$R_{\theta JA}$	55	°C/W	
Thermal Resistance, Junction to Case (Note 5)	$R_{ heta JC}$	30			
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to 150	°C	

Electrical Characteristics Q1 N-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V$, $I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	0.35	_	1.4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D		23	40	mΩ	$V_{GS} = 4.5V, I_D = 4.2A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	26	65	11122	V _{GS} = 2.5V, I _D = 3.3A	
Diode Forward Voltage	V _{SD}	_	0.75	1.2	V	V _{GS} = 0V, I _S = 4.4A	
DYNAMIC CHARACTERISTICS (Note 7)	•			•			
Input Capacitance	C _{iss}		713	_	pF		
Output Capacitance	Coss		80	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	68	_	pF	1 - 1.000112	
Gate Resistance	Rg	_	15	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)		_	8	_	nC		
Total Gate Charge (V _{GS} = 8V)	Qg	_	15	_	nC	10)/ 1 5 5 1	
Gate-Source Charge	Q _{gs}	_	1.0	_	nC	$V_{DS} = 10V, I_{D} = 5.5A$	
Gate-Drain Charge	Q_{gd}	_	1.1	_	nC		
Turn-On Delay Time	t _{D(on)}	_	3.6	_	ns		
Turn-On Rise Time	t _r	_	15.9	_	ns	$V_{DD} = 10V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(off)}	_	16.0	_	ns	$R_L = 2.3\Omega$, $R_G = 1\Omega$	
Turn-Off Fall Time	t _f	_	2.6	_	ns	1	
Body Diode Reverse Recovery Time	trr		6.6	_	nS	I _S = 4.4A, dI/dt = 100A/μs	
Body Diode Reverse Recovery Charge	Qrr	_	1.2	_	nC	$I_S = 4.4A$, $dI/dt = 100A/\mu s$	

Notes:

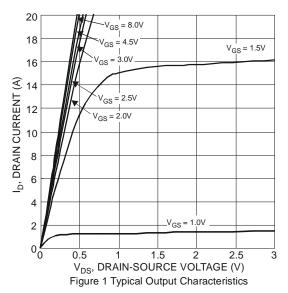
- 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided. 6. Short duration pulse test used to minimize self-heating effect.

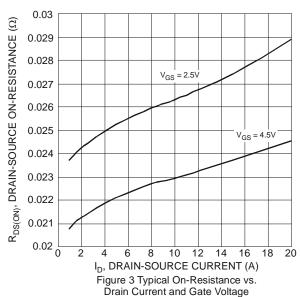
7. Guaranteed by design. Not subject to product testing.

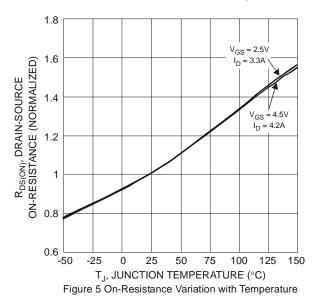
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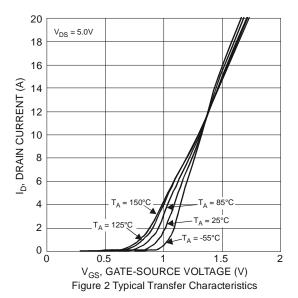
DODES

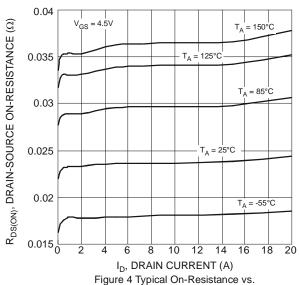






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Drain Current and Temperature

0.05 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) $V_{GS} = 2.5V$ 0.04 = 3.3A 0.03 V_{GS} = 4.5V $I_D = 4.2A$ 0.02 0.01 -50 25 50 75 100 125 T_J, JUNCTION TEMPERATURE (°C) Figure 6 On-Resistance Variation with Temperature

DODES.

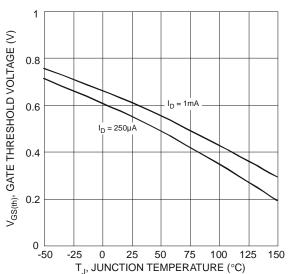
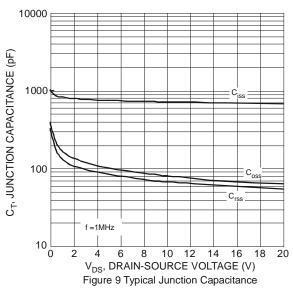
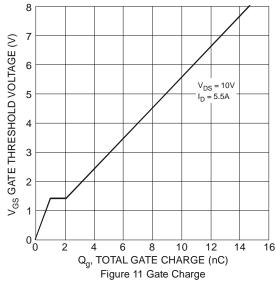
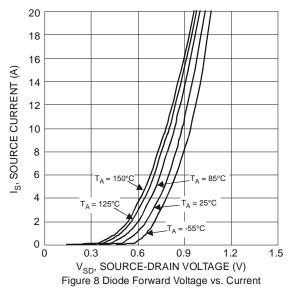


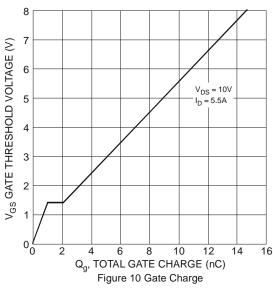
Figure 7 Gate Threshold Variation vs. Ambient Temperature

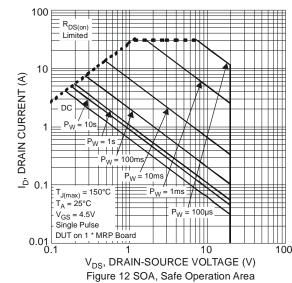




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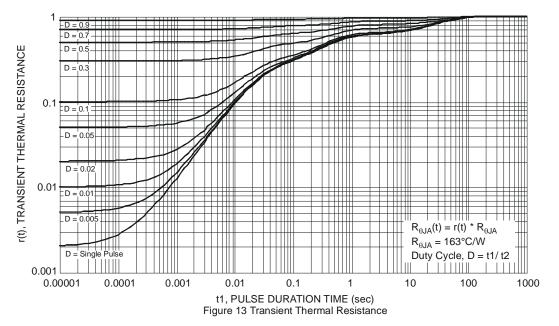


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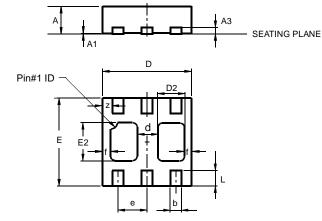


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Package Outline Dimensions

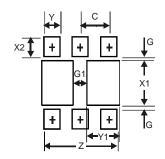
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6								
Type B								
Dim	Min Max Typ							
Α	0.545	0.605	0.575					
A1	0	0.05	0.02					
А3			0.13					
b	0.20	0.30	0.25					
D	1.95	2.075	2.00					
d		_	0.45					
D2	0.50	0.70	0.60					
е	_	_	0.65					
Е	1.95	2.075	2.00					
E2	0.90	1.10	1.00					
f		_	0.15					
L	0.25	0.35	0.30					
z			0.225					
All	Dimens	ions in	mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Υ	0.37
Y1	0.70
С	0.65



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